

EPITAXX

ETX 100GR26

T-41-41

2.6 μm InGaAs Photodiode

Description:

EPITAXX ETX 100GR26 is an InGaAs PIN photodiode which responds to wavelengths up to 2600 nm. The device incorporates a 100 micron diameter compositionally graded InGaAs photodetector mounted in a hermetic TO46 package. The device can be operated either under reverse voltage for optimum speed or photovoltaically for lowest noise. Custom geometries are available by special order.

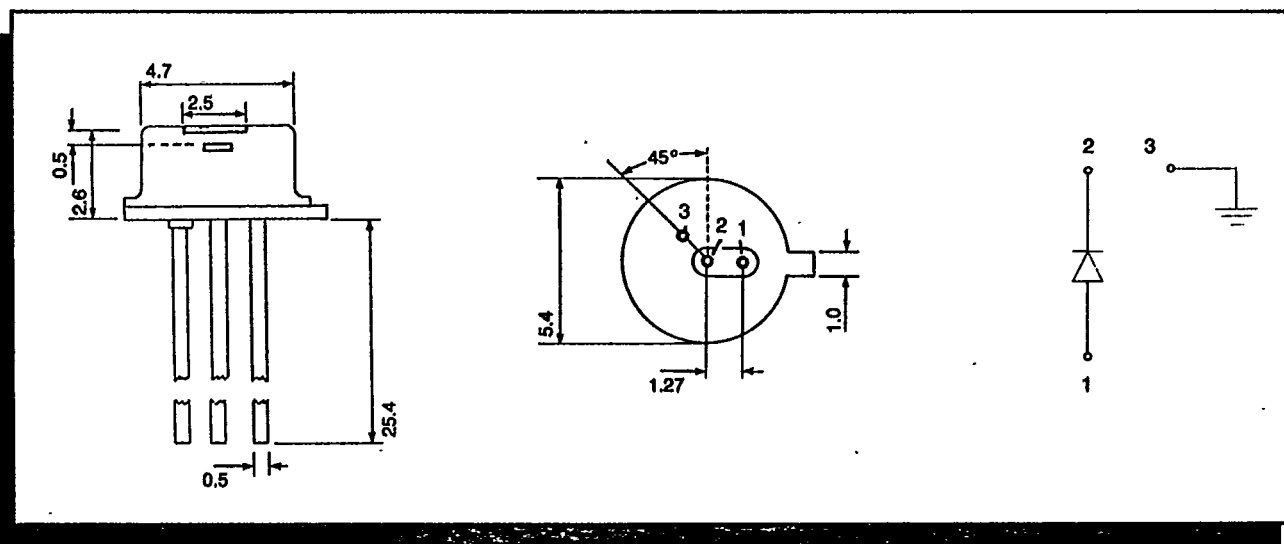
Features:

- 1100 to 2600 nm spectral range
- Room temperature operation
- Photovoltaic
- Low noise

Applications:

- Fire Detection
- NIR Spectroscopy
- Optical Communications
- LIDAR

Dimensions:

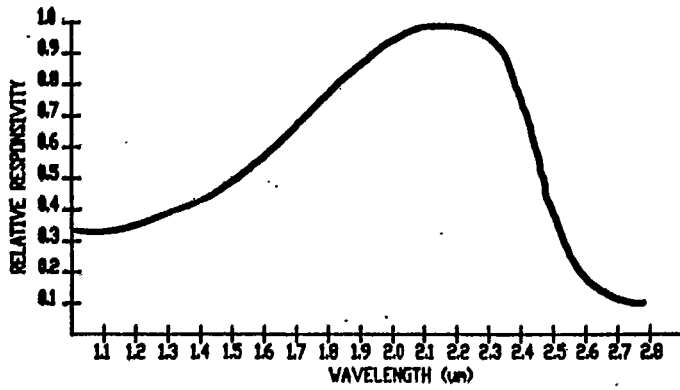
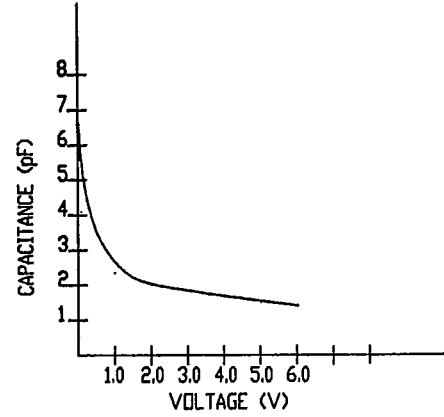
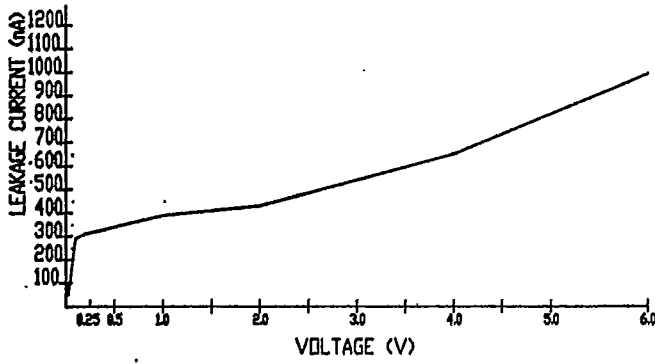


Optical and Electrical Characteristics:

Parameter	Conditions	ETX 100GR 26	Unit
Active area diameter		0.1	mm
Responsivity	@ 2400nm	0.5	A/W
Capacitance	@ -1V	3	pF
Dark Current	@ -1V	500	nA
Shunt Resistance	@ -5mV	100	kOhm
Bandwidth	@ -1V, 3dB	100	MHz
Rise/Fall Time	@ -1V, 50Ω	2	nS

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